



NPN BDX54 – BDX54A – BDX54B – BDX54C

SILICON POWER DARLINGTON TRANSISTORS

The BDX54, BDX54A, BDX54B and BDX54C are silicon epitaxial-base PNP transistors in monolithic Darlington configuration and are mounted in Jedec TO-220 plastic package. They are intended for use in audio amplifiers, medium power linear and switching applications. The complementary NPN types are the BDX53, BDX53A, BDX53B and BDX53C respectively. Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings			Value	Unit
V_{CEO}	Collector-Emitter Voltage	$I_B=0$	BDX54	-45	V
			BDX54A	-60	
			BDX54B	-80	
			BDX54C	-100	
V_{CBO}	Collector-Base Voltage	$I_E=0$	BDX54	-45	V
			BDX54A	-60	
			BDX54B	-80	
			BDX54C	-100	
V_{EBO}	Emitter-Base Voltage	$I_C=0$		-5	V
I_C	Collector Current	$I_{C(RMS)}$		-8	A
		I_{CM}		-12	
I_B	Base Current			-0.2	A
P_T	Power Dissipation	@ $T_C = 25^\circ$		60	W
T_J	Junction Temperature			150	$^\circ\text{C}$
T_S	Storage Temperature			-65 to +150	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	2.08	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

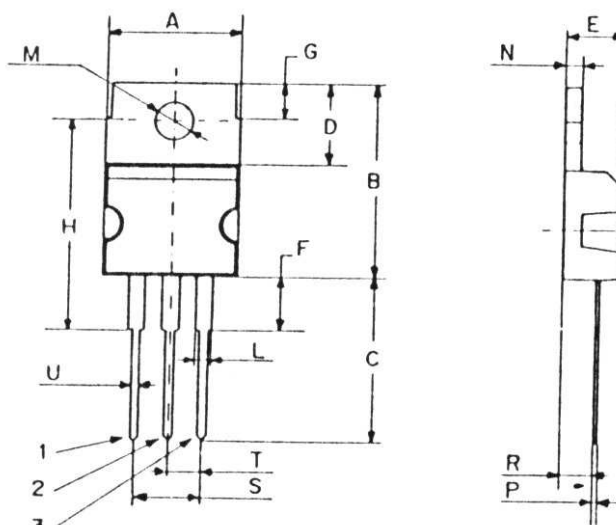
Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit	
$V_{CE(SUS)}$	Collector-Emitter Breakdown Voltage (*)	I_C =-100 mA I_B = 0	BDX54	-45	-	-	V	
			BDX54A	-60	-	-		
			BDX54B	-80	-	-		
			BDX54C	-100	-	-		
I_{CEO}	Collector Cutoff Current	V_{CB} =-22V, I_B = 0	BDX54	-	-	-0.5	mA	
		V_{CB} =-30V, I_B = 0	BDX54A	-	-			
		V_{CB} =-40V, I_B = 0	BDX54B	-	-			
		V_{CB} =-50V, I_B = 0	BDX54C	-	-			
I_{EBO}	Emitter Cutoff Current	V_{BE} =-5 V	BDX54	-	-	-2	mA	
			BDX54A					
			BDX54B					
			BDX54C					
I_{CBO}	Collector-Base Cutoff Current	V_{CBO} =-45 V, I_E = 0	BDX54	-	-	-0.2	mA	
		V_{CBO} =-60 V, I_E = 0	BDX54A	-	-			
		V_{CBO} =-80 V, I_E = 0	BDX54B	-	-			
		V_{CBO} =-100 V, I_E = 0	BDX54C	-	-			
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	I_C =-3 A, I_B =-12 mA	BDX54	-	-	-2	V	
			BDX54A					
			BDX54B					
			BDX54C					
$V_{BE(SAT)}$	Base-Emitter saturation Voltage (*)	I_C =-3 A, I_B =-12 mA	BDX54	-	-	-2.5	V	
			BDX54A					
			BDX54B					
			BDX54C					
V_F	Forward Voltage (pulse method)	I_F =-3 A	BDX54	-	-	-4.0	V	
			BDX54A					
			BDX54B					
			BDX54C					
		I_F =-8 A	BDX54	-	-1.8	-2.5	V	
			BDX54A					
			BDX54B	-	-2.5			
			BDX54C					
h_{FE}	DC Current Gain (*)	V_{CE} =-3 V, I_C =-3 A	BDX54	750	-	-	-	
			BDX54A					
			BDX54B					
			BDX54C					

(*) Pulse Width $\approx 300 \mu\text{s}$, Duty Cycle $\angle 1.5\%$

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MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Case :	Collector

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